



#### FINAL PRODUCT/PROCESS CHANGE NOTIFICATION Generic Copy

## 23-OCT-2002

#### SUBJECT: ON Semiconductor Final Product/Process Change Notification #12594

TITLE: Final Notification for IPCN#12477 - High Frequency, High Voltage NPN Transistors and Switching Diode Transfer from Primarion Fab to ISMF Fab

**EFFECTIVE DATE: 22-Dec-2002** 

AFFECTED CHANGE CATEGORY: ON Semiconductor Fab Site Subcontractor Fab Site

#### **AFFECTED PRODUCT DIVISION: Bipolar Discretes Products Div**

ADDITIONAL RELIABILITY DATA: Available Contact your local ON Semiconductor Sales Office or Laura Rivers <S20636@onsemi.com>

**SAMPLES:** Contact your local ON Semiconductor Sales Office or Barbara Matteson <RM2230@onsemi.com>

## FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact Sales Office or Donald Barlow <R39117@onsemi.com>

#### **DISCLAIMER:**

Final Product/Process Change Notification (FPCN) - Final Notification completing the notification process. Distributed at least 60 days from the effective date of the change. ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact your local ON Semiconductor Sales Office.

#### **DESCRIPTION AND PURPOSE:**

This is the first of three FPCNs that will be issued to complete the changes stated in IPCN #12477 - High Frequency, High Voltage NPN Transistors and Switching Diode Transfer from Primarion Fab to ISMF Fab.

This notification applies only to the finished goods affected device list below. The list is comprised of High Voltage parts that are rated less than 400V. In order to continue to fully support our customer's requirements for High Voltage NPN Transistors the fabrication of these devices is being moved from ON Semiconductor's current subcontractor wafer fab, Primarion in Phoenix Arizona to ON Semiconductor's internal wafer fab ISMF in Seremban, Malaysia.

# **ON Semiconductor**



Final Product/Process Change Notification #12594

## **RELIABILITY DATA SUMMARY:**

#### **Qualification Vehicle: MMBTA42LT1**

TEST:	CONDITIONS	INTERVAL	SIZE	FAILURES
Autoclave	Ta=121DegC , RH=100%, P=15 psig,	0 96	240 240	0/240 0/240
Temperature Cycle	Ta=65/+150DegC, Air to Air, Dwell equal to or greater than 15 Min., Transfer equal to or less than 10 M	0 500 1000 Iin.	240 240 240	0/240 0/240 0/240
IOL	Ton=2 min, Toff=2min, Ta=25 DegC	7500 cycles 15000 cycles	240 240	0/240 0/240
External Visual	Equal to or greater than Mid-Std-750, Method 2071	N/M	100%	
D.P.A	Random sample of good Temp Cycle and H3TRB devices p CDF-AEC-Q101-004 Section	N/M per	6	Passed
Die Bond (Die Shear)	In-process assembly	N/M	15	Passed
Wire Bond (Pull)	In-process assembly	N/M	15	Passed
High Humidity High Temp. Reverse Bias	Ta=+85DegC, RH=85% VCB = 100V	0 504 1008	240 240 240	0/240 0/240 0/240
High Temp. Reverse Bias	Ta=+150DegC VCB = 240V	0 504 1008	240 240 240	0/240 0/240 0/240
Electro Static Discharge	Human Body Model & Machine Models 1 & 2	N/M	HBM MM	>16kV >400V

# **Reliability Testing Conclusions:**

Test results meet all quality and reliability requirements.

# **ELECTRICAL CHARACTERISTIC SUMMARY:**

Electrical characterization of the old and new process showed equal or better performance by the new product. Data is available upon request.

# CHANGED PART IDENTIFICATION:

No changes to the Physical part. Product with date codes after WW51 may come from either site.

# **ON Semiconductor**



Final Product/Process Change Notification #12594

# AFFECTED DEVICE LIST (WITHOUT SPECIALS):

PART BF393 BF393ZL1 MMBTA42LT1 MMBTA42LT3 MMBTA43LT1 MPSA42 MPSA42RL1 MPSA42RLRA MPSA42RLRE MPSA42RLRF MPSA42RLRM MPSA42RLRP MPSA42ZL1 MPSA43 MPSA43RLRA MPSA43ZL1 MPSW42 MPSW42RLRA MSD42T1 MSD42WT1 PZTA42T1